

# NPN SILICON PLANAR TRANSISTORS

## 2N1893



TO-39

#### **APPLICATION:** General Purpose Transistor

#### **ABSOLUTE MAXIMUM RATINGS** (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector Emitter Voltage	V <sub>CEO</sub>	80	V
Collector Emitter Voltage	V <sub>CER</sub>	100	V
Collector Base Voltage	V <sub>CBO</sub>	120	V
Emitter Base Voltage	V <sub>EBO</sub>	7.0	V
Collector Current Continuous	Ι <sub>c</sub>	0.5	А
Total Device Dissipation @ T <sub>a</sub> =25°C	Б	0.8	W
Derate Above 25°C	PD	4.57	mW/°C
Total Device Dissipation@ T <sub>c</sub> =25°C	P <sub>D</sub>	3.0	W
Derate Above 25°C	۲D	17.2	mW/°C
Operating And Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-65 to +200	°C

#### **Thermal Resistance**

Junction to Ambient	$R_{th(j-a)}$	219	°C/W
Junction to Case	$R_{th(j-c)}$	58.3	C/VV





#### ELECTRICAL CHARACTERISTICS at (Ta = 25 °C Unless otherwise specified)

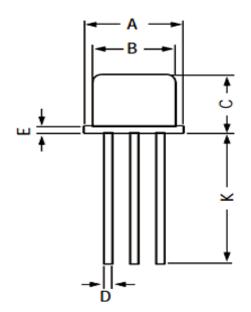
PARAMETER	SYMBOL	TEST CONDITION	VALUE			
PARAMETER	STMBUL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector Emitter Breakdown Voltage	$BV_{CER(sus)}$	$I_{C}$ =100mA, $R_{BE}$ =10 $\Omega$	100	-		V
Collector Emitter Sustaining Voltage	BV <sub>CEO(sus)</sub> <sup>1</sup>	I <sub>C</sub> =10mA,I <sub>B</sub> =0	80	-		V
Collector Base Breakdown Voltage	BV <sub>CBO</sub>	Ι <sub>C</sub> =100μΑ,Ι <sub>E</sub> =0	120			V
Emitter Base Breakdown Voltage	$BV_{EBO}$	Ι <sub>Ε</sub> =100μΑ,Ι <sub>C</sub> =0	7.0			V
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =90V, I <sub>E</sub> =0			10	nA
	СВО	V <sub>CB</sub> =90V, I <sub>E</sub> =0,T <sub>A</sub> =150°C			15	μA
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{EB}$ =5V,I <sub>C</sub> =0			10	nA
		I <sub>C</sub> =1mA,V <sub>CE</sub> =10V	20	I		-
DC Current Gain	h <sub>FE</sub> <sup>1</sup>	I <sub>C</sub> =10mA,V <sub>CE</sub> =10V	35	ł		-
DC Current Gain	<sup>II</sup> FE	I <sub>C</sub> =10mA,V <sub>CE</sub> =10V,T <sub>C</sub> =-55°C	20	ł		-
		I <sub>C</sub> =150mA,V <sub>CE</sub> =10V	40	-	120	
Collector Emitter (Sat) Voltage	V <sub>CE(Sat)</sub>	I <sub>C</sub> =50mA,I <sub>B</sub> =5.0mA		-	1.2	V
		I <sub>C</sub> =150mA,I <sub>B</sub> =15mA		-	5.0	V
Base Emitter (Sat) Voltage	$V_{BE(Sat)}$	I <sub>C</sub> =50mA,I <sub>B</sub> =5.0mA		I	0.9	V
, <i>,</i> , ,		I <sub>C</sub> =150mA,I <sub>B</sub> =15mA			1.3	
SMALL SIGNAL CHARACTERISTICS						
Current Gain Bandwidth Product	f <sub>T</sub>	I <sub>C</sub> =50mA, V <sub>CE</sub> =10V,f=20MHz	50			MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			15	рF
Input Capacitance	C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1MHz		-	85	рF
land have been	h <sub>ib</sub>	I <sub>C</sub> =1.0mA,V <sub>CB</sub> =5.0V,f=1.0kHz	20	-	30	Ω
Input Impedance		I <sub>C</sub> =5.0mA,V <sub>CB</sub> =10V,f=1.0kHz	4.0		8.0	
Voltaga Faadhaak Datia	h	I <sub>C</sub> =1.0mA,V <sub>CB</sub> =5.0V,f=1.0kHz			1.25	X10 <sup>-4</sup>
Voltage Feedback Ratio	h <sub>rb</sub>	I <sub>C</sub> =5.0mA,V <sub>CB</sub> =10V,f=1.0kHz			1.5	
Small Signal Current Gain	h <sub>fe</sub>	I <sub>C</sub> =1.0mA, V <sub>CB</sub> =5.0V,f=1.0kHz	30		100	
Output Admittance	h <sub>ob</sub>	I <sub>C</sub> =1.0mA,V <sub>CB</sub> =5.0V,f=1.0kHz			0.5	µmho
	<b>''</b> ob	I <sub>C</sub> =5.0mA,V <sub>CB</sub> =10V,f=1.0kHz			0.5	

Note:

1. Pulse Test: Pulse Width <300µs, Duty Cycle <2%



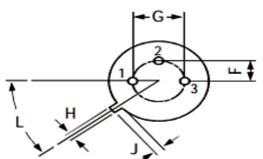
## PACKAGE DETAILS



#### DIM MIN MAX А 8.50 9.39 В 7.74 8.50 С 6.60 6.09 0.53 D 0.40 Е -0.88 F 2.66 2.41 G 4.82 5.33 0.71 Н 0.86 J 0.73 1.02 Κ 12.70 -L 42 DEG 48 DEG

All Dimension are in mm

**TO-39 Metal Can Package** 



#### **PIN CONFIGURATION**

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR

#### Packing Detail

PACKAGE	STAND/	ARDPACK	INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	GrWt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

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### Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

#### Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

#### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level			
Level	Time	Condition	
1	Unlimited	≤30 °C / 85% RH	
2	1 Year	≤30 °C / 60% RH	
2a	4 Weeks	≤30 °C / 60% RH	
3	168 Hours	≤30 °C / 60% RH	
4	72 Hours	≤30 °C / 60% RH	
5	48 Hours	≤30 °C / 60% RH	
5a	24 Hours	≤30 °C / 60% RH	
6	Time on Label(TOL)	≤30 °C / 60% RH	





#### **Customer Notes**

#### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

#### Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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